STD90N03L
STD90N03L-1

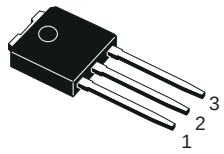
N-channel 30V - 0.005Ω - 80A - DPAK/IPAK
STripFET™ III Power MOSFET

General features

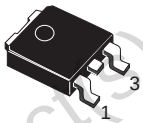
Type	V_{DSS}	$R_{DS(on)}$	I_D
STD90N03L	30V	0.0057Ω	80A (1)
STD90N03L-1	30V	0.0057Ω	80A (1)

1. Pulse width limited by safe operating area

- $R_{DS(on)}$*Q_g industry's benchmark
- Conduction losses reduced
- Switching losses reduced
- Low threshold device



IPAK



DPAK

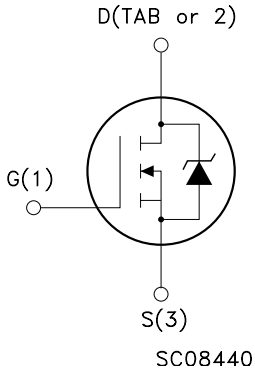
Description

This device utilizes the latest advanced design rules of ST's proprietary STripFET™ technology. This is suitable for the most demanding DC-DC converter application where high efficiency is to be achieved.

Applications

- Switching applications

Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STD90N03L	D90N03L	DPAK	Tape & reel
STD90N03L-1	D90N03L-1	IPAK	Tube

Content

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	30	V
V_{GS}	Gate-source voltage	±20	V
I_D(1)	Drain current (continuous) at T_C = 25°C	80	A
I_D	Drain current (continuous) at T_C=100°C	64	A
I_{DM}(2)	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at T_C = 25°C	95	W
	Derating factor	0.63	W/°C
E_{AS}(3)	Single pulse avalanche energy	350	mJ
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 175	°C

1. Value limited by wire bonding
2. Pulse width limited by safe operating area
3. Starting T_j = 25°C, I_D =40A, V_{DD} =15V

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	1.58	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient max	100	°C/W
T_j	Maximum lead temperature for soldering purpose	275	°C

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 250µA, V_{GS}= 0	30			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 30V V_{DS} = 30V, Tc=125°C			1 10	µA µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ±20V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 250µA	1			V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS}= 10V, I_D= 40A V_{GS}= 5V, I_D= 40A		0.005 0.007	0.0057 0.0011	Ω Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} =25V, f=1MHz, V_{GS}=0		2805 549 76		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD}=15V, I_D = 80A V_{GS} =5V *(see Figure 13)*		22 10 7	32	nC nC nC
R_G	Gate input resistance	f=1MHz Gate Bias Bias=0 Test Signal Level=20mV open drain		1.2		Ω

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	V_{DD}=15V, I_D=40A, R_G=4.7Ω, V_{GS}=5V *(see Figure 12)*		19 135		ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	V_{DD}=15V, I_D=40A, R_G=4.7Ω, V_{GS}=5V *(see Figure 12)*		24 33		ns ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (1)	Source-drain current Source-drain current (pulsed)				80 320	A A
V_{SD} (2)	Forward on voltage	I_{SD}=40A, V_{GS}=0			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}=80A, di/dt = 100A/µs, V_{DD}=19 V, Tj= 150°C *(see Figure 15)*		36 32 1.8		ns µC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

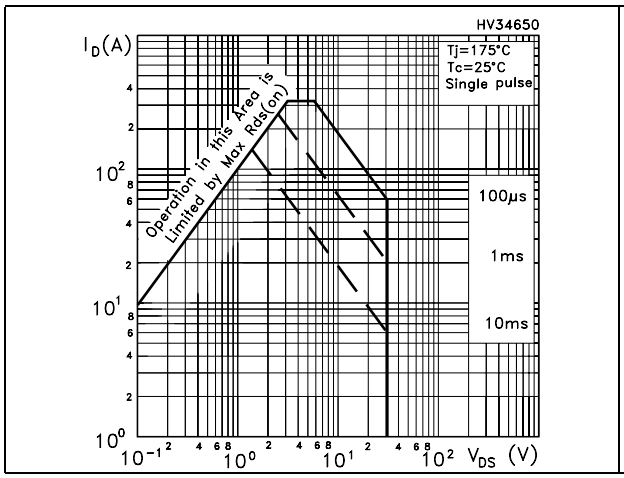


Figure 2. Thermal impedance

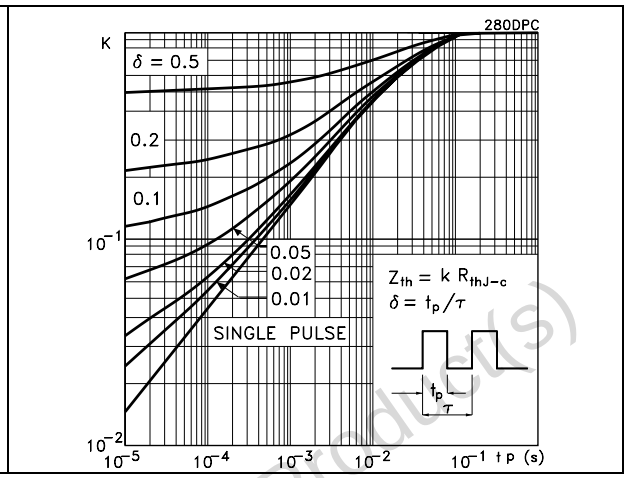


Figure 3. Output characteristics

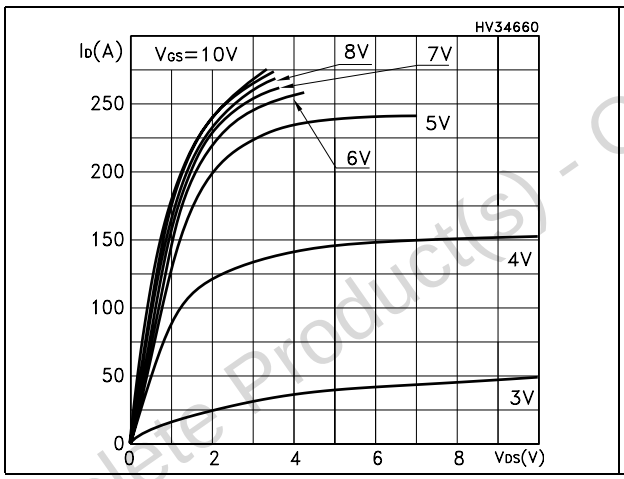


Figure 4. Transfer characteristics

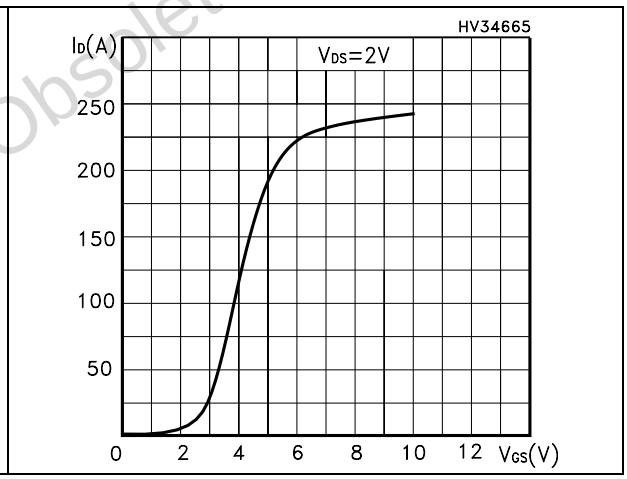


Figure 5. Static drain-source on resistance

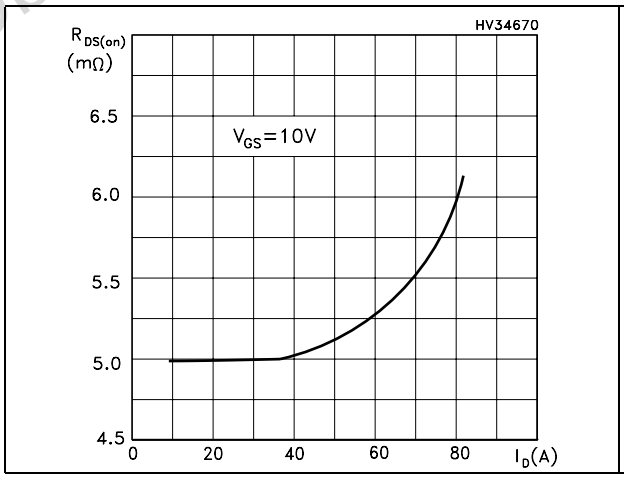


Figure 6. Normalized B_{VDSS} vs temperature

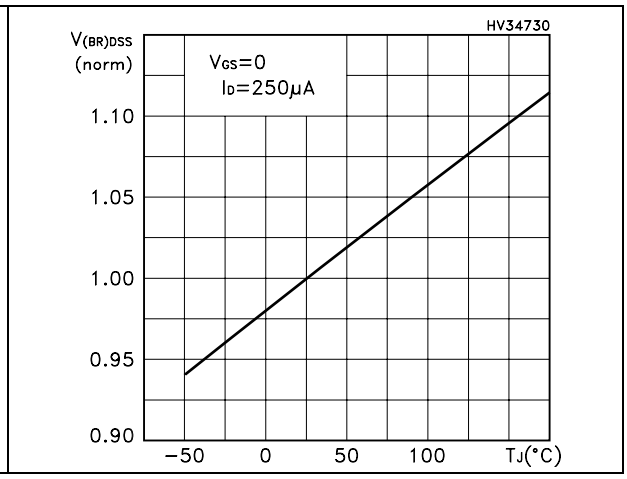


Figure 7. Gate charge vs gate-source voltage

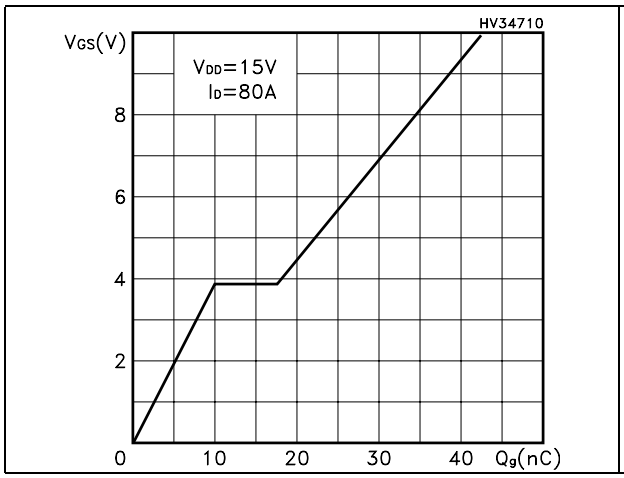


Figure 8. Capacitance variations

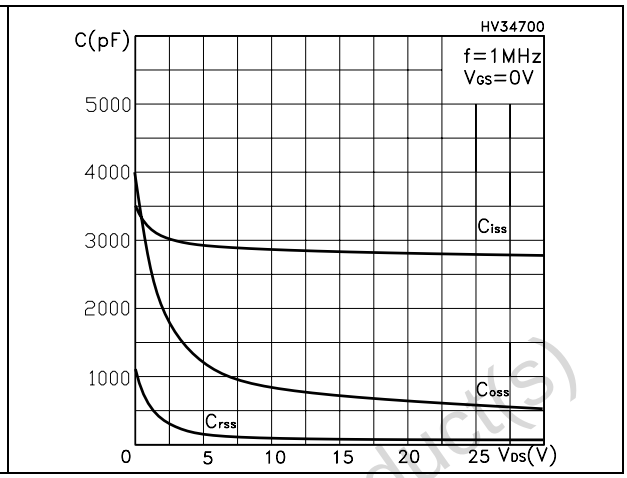


Figure 9. Normalized gate threshold voltage vs temperature

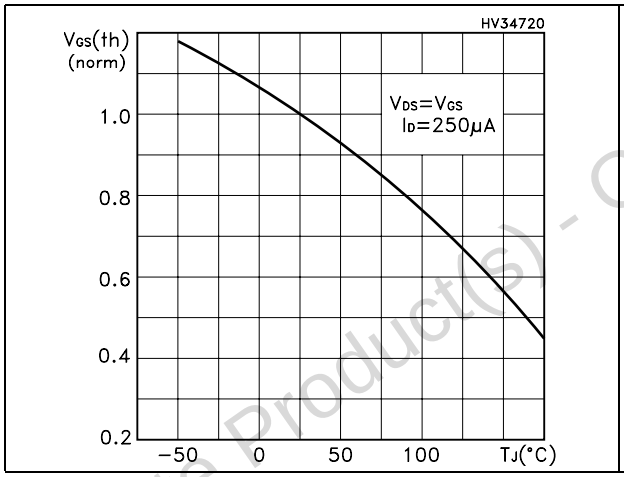


Figure 10. Normlaized on resistance vs temperature

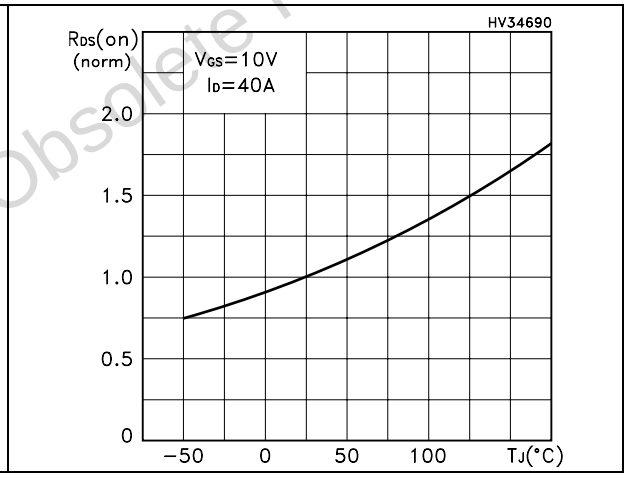
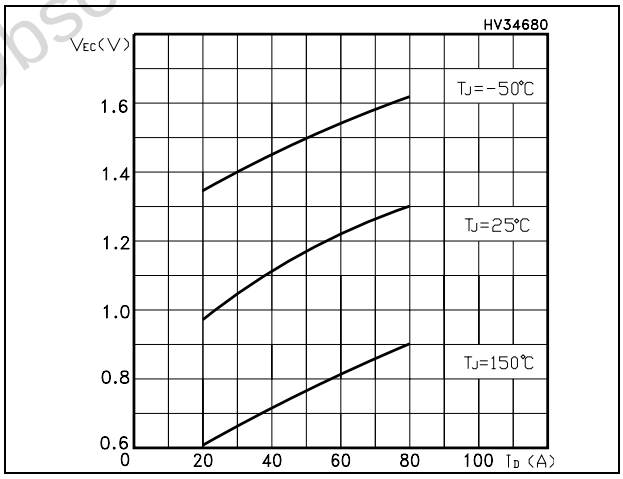


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load

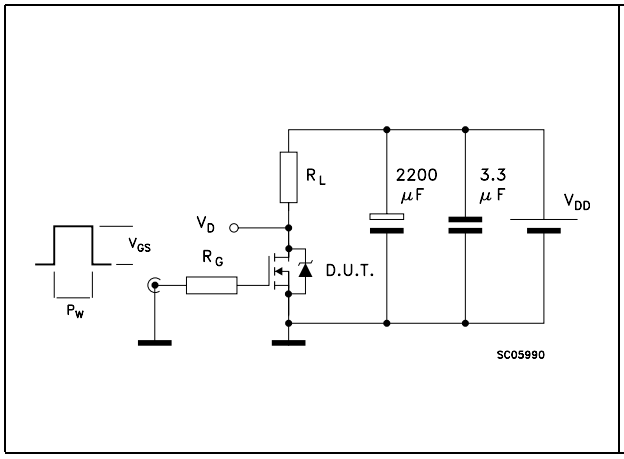


Figure 13. Gate charge test circuit

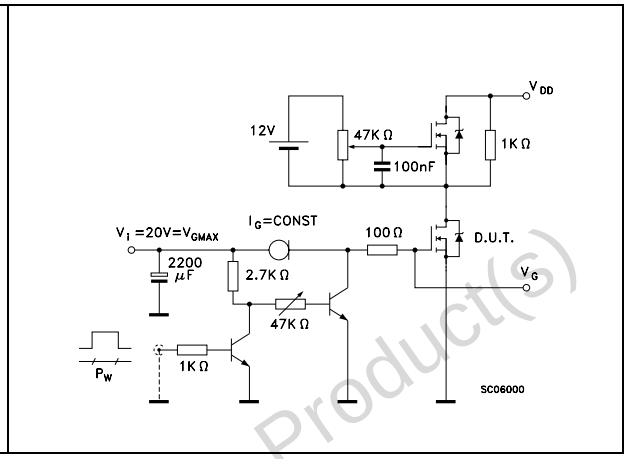


Figure 14. Test circuit for inductive load switching and diode recovery times

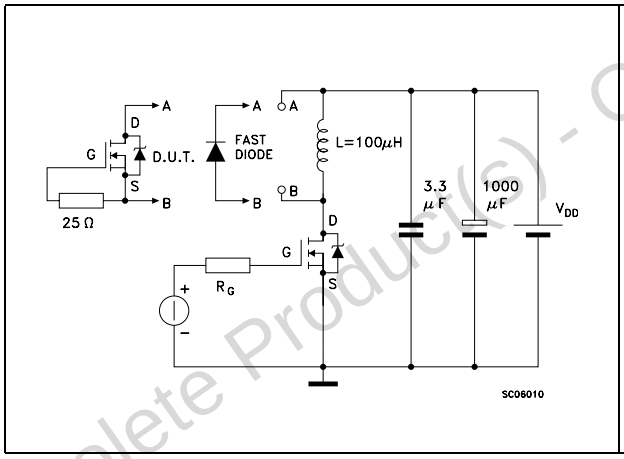
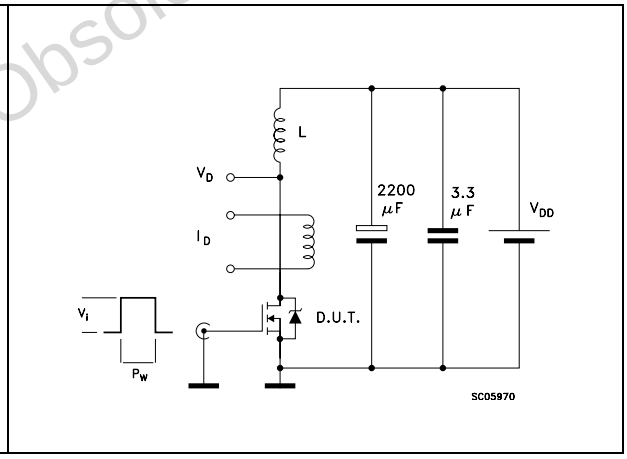
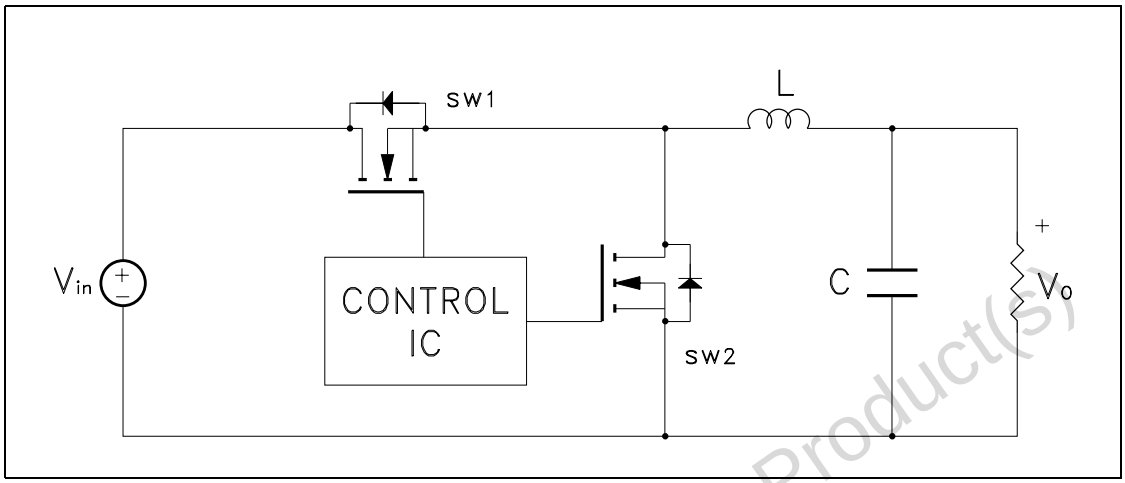


Figure 15. Unclamped Inductive load test circuit



Appendix A

Figure 16. Buck Converter: Power Losses Estimation



The power losses associated with the FETs in a Synchronous Buck converter can be estimated using the equations shown in the table below. The formulas give a good approximation, for the sake of performance comparison, of how different pairs of devices affect the converter efficiency. However a very important parameter, the working temperature, is not considered. The real device behavior is really dependent on how the heat generated inside the devices is removed to allow for a safer working junction temperature.

The low side (SW2) device requires:

- Very low $R_{DS(on)}$ to reduce conduction losses
- Small Qgls to reduce the gate charge losses
- Small Coss to reduce losses due to output capacitance
- Small Qrr to reduce losses on SW1 during its turn-on
- The Cgd/Cgs ratio lower than Vth/Vgg ratio especially with low drain to source
- voltage to avoid the cross conduction phenomenon;

The high side (SW1) device requires:

- Small Rg and Ls to allow higher gate current peak and to limit the voltage feedback on the gate
- Small Qg to have a faster commutation and to reduce gate charge losses
- Low $R_{DS(on)}$ to reduce the conduction losses.

Table 7. Power losses calculation

		High Side Switching (SW1)	Low Side Switch (SW2)
$P_{conduction}$		$R_{DS(on)SW1} * I_L^2 * \delta$	$R_{DS(on)SW2} * I_L^2 * (1-\delta)$
$P_{switching}$		$V_{in} * (Q_{gsth(SW1)} + Q_{gd(SW1)}) * f * \frac{I_L}{I_g}$	Zero voltage switching
P_{diode}	Recovery (1)	Not applicable	$V_{in} * Q_{rr(SW2)} * f$
	Conduction	Not applicable	$V_{f(SW2)} * I_L * t_{deadtime} * f$
$P_{gate(QG)}$		$Q_{g(SW1)} * V_{gg} * f$	$Q_{gls(SW2)} * V_{gg} * f$
P_{Qoss}		$\frac{V_{in} * Q_{oss(SW1)} * f}{2}$	$\frac{V_{in} * Q_{oss(SW2)} * f}{2}$

1. Dissipated by SW1 during turn-on

Table 8. Paramiters meaning

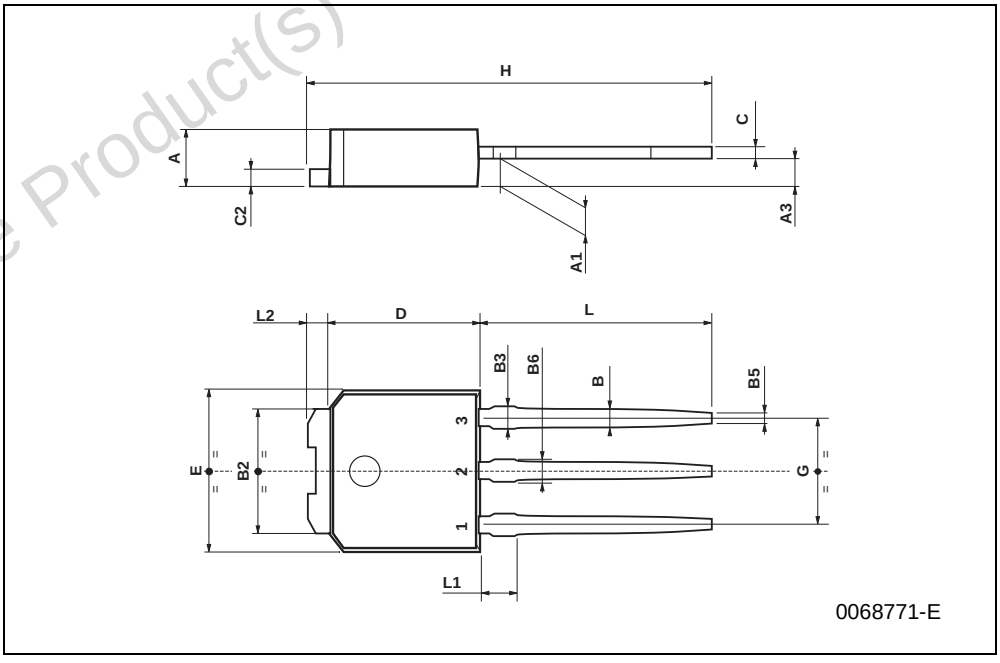
Parameter	Meaning
d	Duty-cycle
Q_{gsth}	Post threshold gate charge
Q_{gls}	Third quadrant gate charge
$P_{conduction}$	On state losses
$P_{switching}$	On-off transition losses
P_{diode}	Conduction and reverse recovery diode losses
P_{gate}	Gate drive losses
P_{Qoss}	Output capacitance losses

4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: *www.st.com*

TO-251 (IPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



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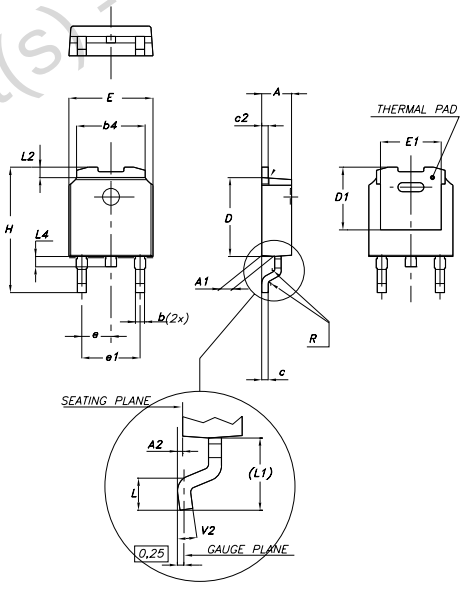
DPAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
e		2.28			0.090	
e1	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°



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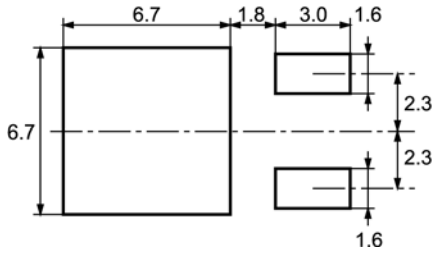
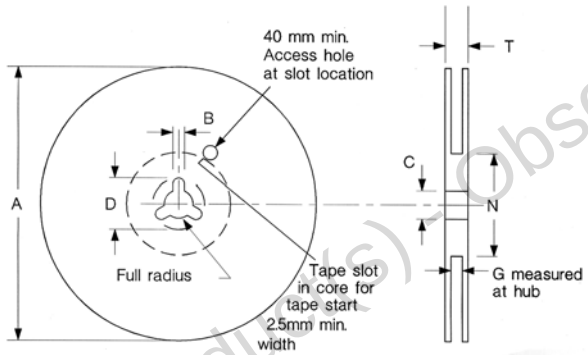
5 Packaging mechanical data

DPAK FOOTPRINT



All dimensions are in millimeters

TAPE AND REEL SHIPMENT



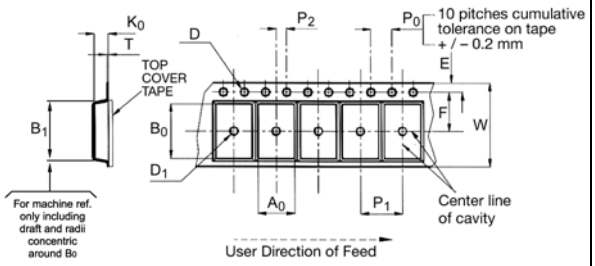
REEL MECHANICAL DATA

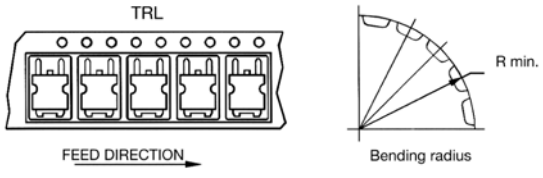
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641





6 Revision history

Table 9. Revision history

Date	Revision	Changes
20-Oct-2006	1	Initial release.

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